

# 2SA2166

FOR GENERAL PURPOSE HIGH CURRENT DRIVE APPLICATION  
SILICON PNP EPITAXIAL TYPE

## DESCRIPTION

ISAHAYA 2SA2166 is a silicon PNP epitaxial type transistor designed with high collector current, low  $V_{CE(sat)}$ .

## FEATURE

- High collector current

$$I_{C(MAX)} = -500\text{mA}$$

- Low collector to emitter saturation voltage

$$V_{CE(sat)} < -0.4V_{max} (I_C = -150\text{mA}, I_B = -15\text{mA})$$

## APPLICATION

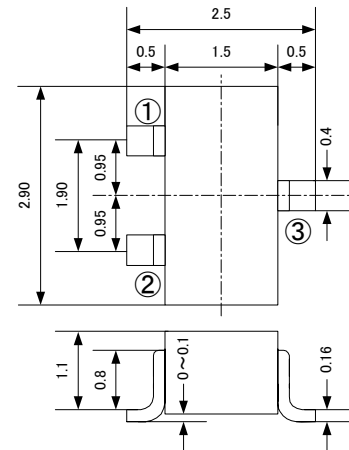
For switching application, small type motor drive application.

## MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

記号	項目	定格値	単位
$V_{CEO}$	Collector to Emitter voltage	-60	V
$V_{CBO}$	Collector to Base voltage	-60	V
$V_{EBO}$	Emitter to Base voltage	-5	V
$I_C$	Collector current	-500	mA
$P_C$	Collector dissipation	200	mW
$T_j$	Junction temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage temperature	-55~150	$^\circ\text{C}$

## OUTLINE DRAWING

Unit: mm

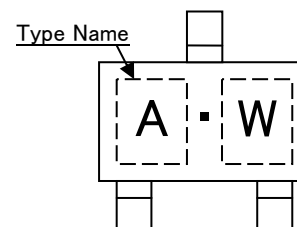


**Notice:** The dimension without tolerance represent central value.

### TERMINAL CONNECTOR

- ①: BASE                      EIAJ: SC-59
- ②: EMITTER                JEDEC: TO-236
- ③: COLLECTOR             Resemblance

## MARKING

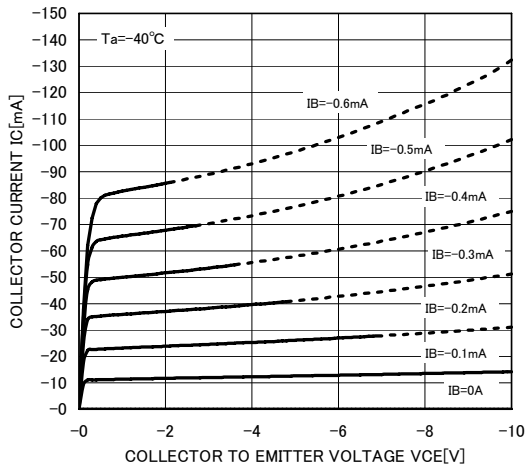


## ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

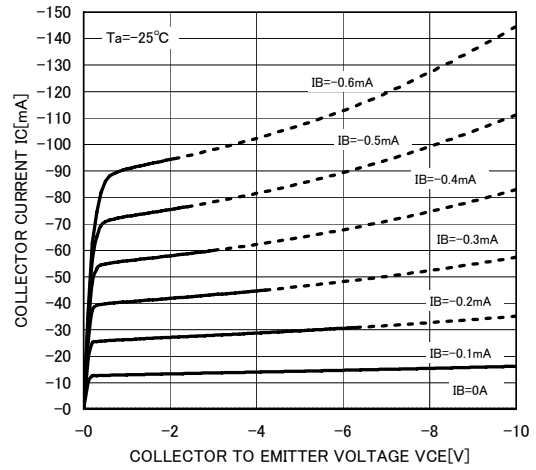
Symbol	Parameter	Test condition	Limits			Unit
			Min	Typ	Max	
$V_{(BR)CEO}$	C to E break down voltage	$I_C = -1\text{mA}, I_B = 0$	-60			V
$V_{(BR)CBO}$	C to B break down voltage	$I_C = -10\mu\text{A}, I_E = 0$	-60			V
$V_{(BR)EBO}$	E to B break down voltage	$I_E = -10\mu\text{A}, I_C = 0$	-5			V
$I_{CBO}$	Collector cut off current	$V_{CB} = -50\text{V}, I_E = 0$			-100	nA
$I_{EBO}$	Emitter cut off current	$V_{EB} = -3\text{V}, I_C = 0$			-100	nA
$h_{FE}$	DC forward current gain	$I_C = -150\text{mA}, V_{CE} = -10\text{V}$	100		300	---
$V_{CE(sat)}$	C to E saturation voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$			-0.4	V
$V_{BE(sat)}$	B to E saturation voltage	$I_C = -150\text{mA}, I_B = -15\text{mA}$			-1.3	V
$f_T$	Gain band width product	$I_E = 50\text{mA}, V_{CE} = -20\text{V}, f = 100\text{MHz}$	200			MHz
$C_{ob}$	Collector output capacitance	$V_{CB} = -10\text{V}, f = 1\text{MHz}$			8	pF

## TYPICAL CHARACTERISTICS

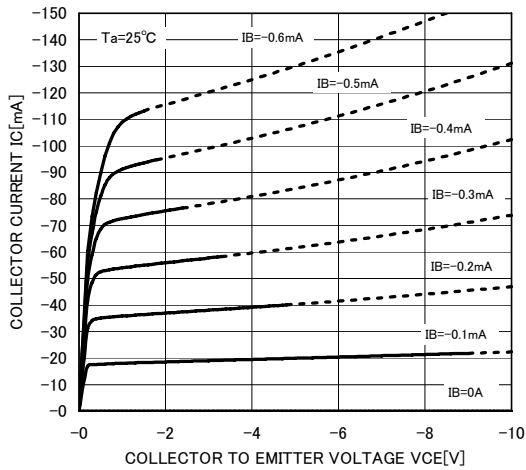
COMMON EMITTER OUTPUT



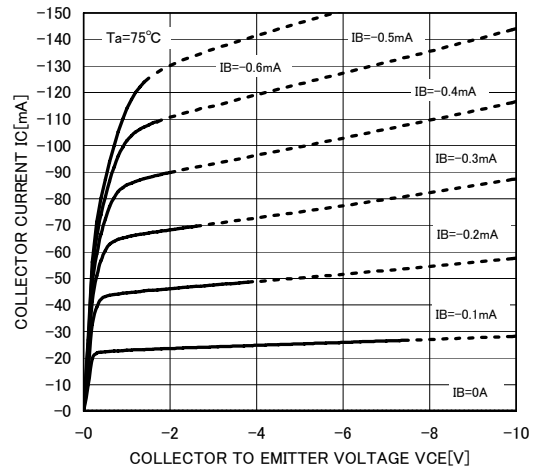
COMMON EMITTER OUTPUT



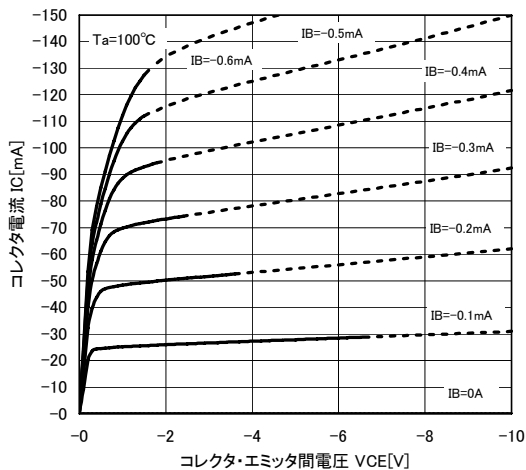
COMMON EMITTER OUTPUT



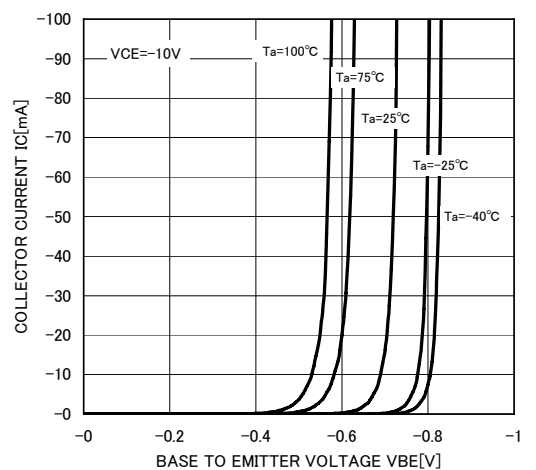
COMMON EMITTER OUTPUT



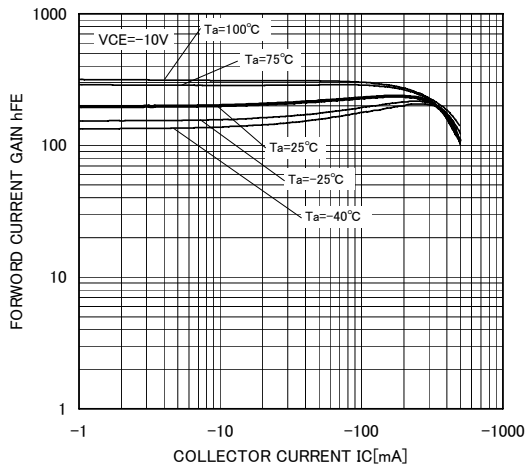
エミッタ接地出力特性



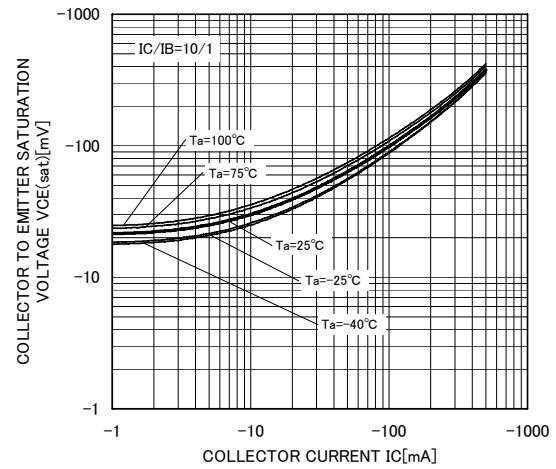
COMMON EMITTER TRANSFER



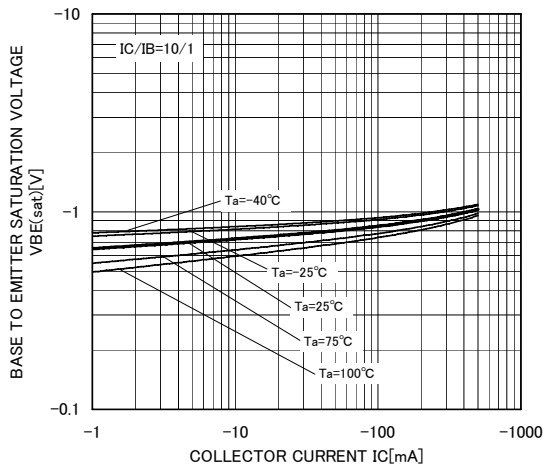
DC FORWARD CURRENT GAIN  
VS. COLLECTOR CURRENT



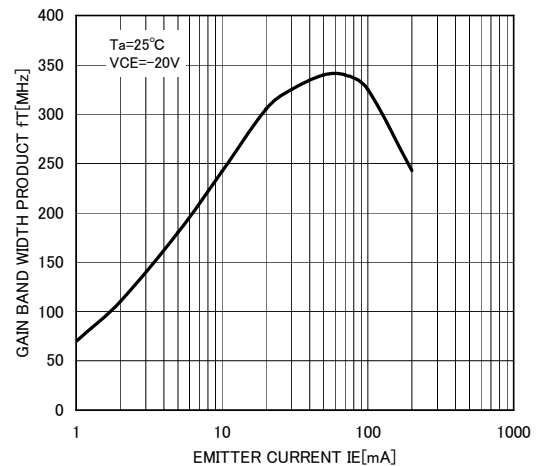
COLLECTOR TO EMITTER SATURATION VOLTAGE  
VS. COLLECTOR CURRENT



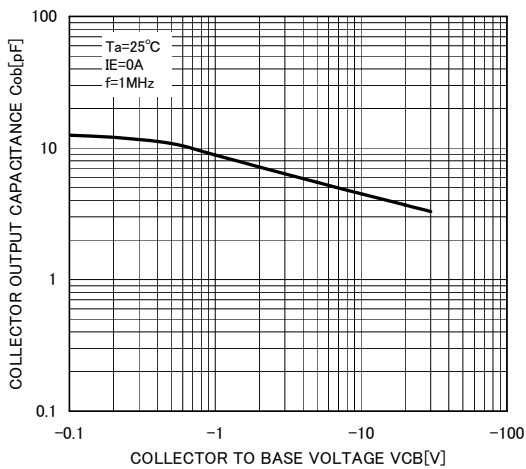
BASE TO EMITTER SATURATION VOLTAGE  
VS. COLLECTOR CURRENT



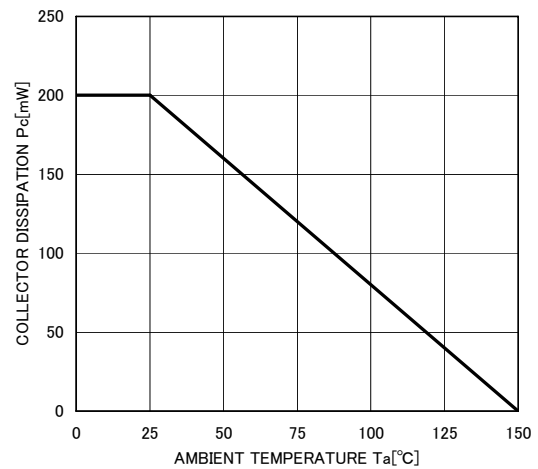
GAIN BAND WIDTH PRODUCT  
VS. EMITTER CURRENT



COLLECTOR OUTPUT CAPACITANCE  
VS. COLLECTOR TO BASE VOLTAGE



COLLECTOR DISSIPATION  
VS. AMBIENT TEMPERATURE





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